

isc Silicon PNP Power Transistor
BD950F/952F/954F/956F
DESCRIPTION

- DC Current Gain-
: $h_{FE} = 40(\text{Min}) @ I_C = -500\text{mA}$
- Complement to Type BD949F/951F/953F/955F
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

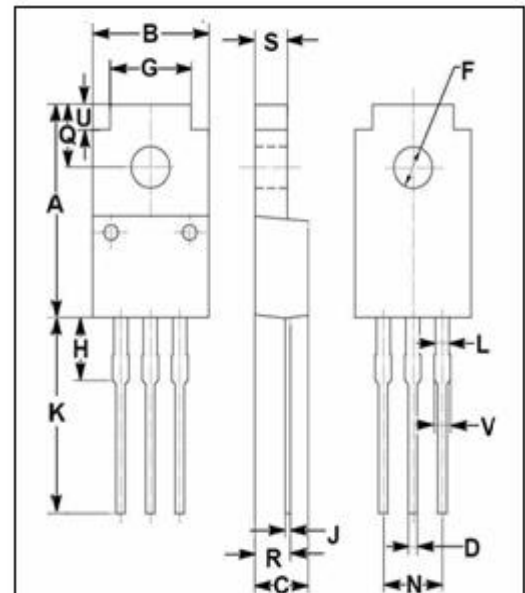
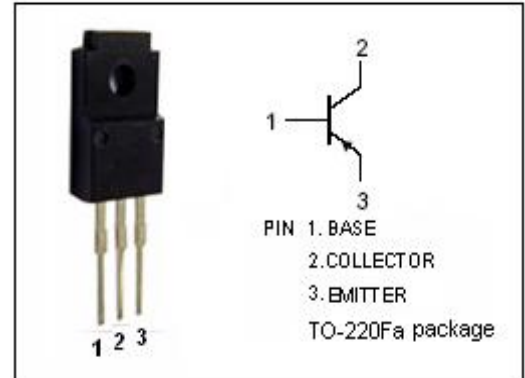
- Designed for power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	BD950F	-60	V
		BD952F	-80	
		BD954F	-100	
		BD956F	-120	
V_{CEO}	Collector-Emitter Voltage	BD950F	-60	V
		BD952F	-80	
		BD954F	-100	
		BD956F	-120	
V_{EBO}	Emitter-Base Voltage	-5	V	
I_C	Collector Current-Continuous	-5	A	
I_{CM}	Collector Current-Peak	-8	A	
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	22	W	
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-65~150	$^\circ\text{C}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	8.12	$^\circ\text{C/W}$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.54	10.10
C	4.35	4.65
D	0.75	0.90
F	3.20	3.40
G	6.90	7.20
H	3.80	4.20
J	0.45	0.75
K	13.35	13.80
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.55	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CE0(SUS)}	Collector-Emitter Sustaining Voltage	I _C = -30mA ; I _B = 0	BD950F	-60			V
			BD952F	-80			
			BD954F	-100			
			BD956F	-120			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			-1.0	V	
V _{BE(on)}	Base-Emitter On Voltage	I _C = -2A; V _{CE} = -4V			-1.4	V	
I _{CBO}	Collector Cutoff Current	V _{CB} = V _{CB0max} ; I _E = 0 V _{CB} = 1/2V _{CB0max} ; I _E = 0, T _J =150°C			-0.05 -1	mA	
I _{CEO}	Collector Cutoff Current	V _{CE} = V _{CE0max} ; I _B = 0			-0.1	mA	
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-0.2	mA	
h _{FE-1}	DC Current Gain	I _C = -500mA ; V _{CE} = -4V	40				
h _{FE-2}	DC Current Gain	I _C = -2A ; V _{CE} = -4V		20			
f _T	Current-Gain—Bandwidth Product	I _C = -500mA ; V _{CE} = -4V	3			MHz	

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